1N5908

Preferred Device

1500 Watt Mosorb™ Zener Transient Voltage Suppressors

Unidirectional*

Mosorb devices are designed to protect voltage sensitive components from high voltage, high-energy transients. They have excellent clamping capability, high surge capability, low zener impedance and fast response time. These devices are ON Semiconductor's exclusive, cost-effective, highly reliable Surmetic™ axial leaded package and are ideally-suited for use in communication systems, numerical controls, process controls, medical equipment, business machines, power supplies and many other industrial/consumer applications, to protect CMOS, MOS and Bipolar integrated circuits.

Features

- Working Peak Reverse Voltage Range 5.0 V
- Peak Power 1500 Watts @ 1 ms
- Maximum Clamp Voltage @ Peak Pulse Current
- Low Leakage < 5 µA Above 10 V
- Response Time is Typically < 1 ns
- These are Pb-Free Devices*

Mechanical Characteristics

CASE: Void-free, transfer-molded, thermosetting plastic

FINISH: All external surfaces are corrosion resistant and leads are

readily solderable

MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES:

260°C, 1/16" from the case for 10 seconds **POLARITY:** Cathode indicated by polarity band

MOUNTING POSITION: Any



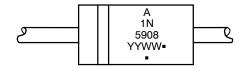
ON Semiconductor®





AXIAL LEAD CASE 41A PLASTIC

MARKING DIAGRAM



A = Assembly Location 1N5908 = JEDEC Device Number

YY = Year WW = Work Week = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
1N5908G	Axial Lead (Pb-Free)	500 Units/Box
1N5908RL4G	Axial Lead (Pb-Free)	1500/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MAXIMUM RATINGS

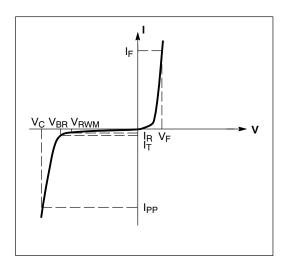
Rating	Symbol	Value	Unit
Peak Power Dissipation (Note 1) @ T _L ≤ 25°C	P _{PK}	1500	W
Steady State Power Dissipation @ $T_L \le 75^{\circ}$ C, Lead Length = $3/8''$	P_{D}	5.0	W
Derated above T _L = 75°C		50	mW/°C
Thermal Resistance, Junction-to-Lead	$R_{ heta JL}$	20	°C/W
Forward Surge Current (Note 2) @ T _A = 25°C	I _{FSM}	200	Α
Operating and Storage Temperature Range	T _J , T _{stg}	- 65 to +175	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- Nonrepetitive current pulse per Figure 4 and derated above T_A = 25°C per Figure 2.
 1/2 sine wave (or equivalent square wave), PW = 8.3 ms, duty cycle = 4 pulses per minute maximum.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted, $V_F = 3.5 \text{ V Max.}$ @ I_F (Note 3) = 100 A)

Symbol	Parameter					
I _{PP}	Maximum Reverse Peak Pulse Current					
V _C	Clamping Voltage @ IPP					
V _{RWM}	Working Peak Reverse Voltage					
I _R	Maximum Reverse Leakage Current @ V _{RWM}					
V _{BR}	Breakdown Voltage @ I _T					
I _T	Test Current					
IF	Forward Current					
V _F	Forward Voltage @ I _F					



Uni-Directional TVS

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted, $V_F = 3.5 \text{ V Max.}$ @ I_F (Note $3^{\circ} = 53 \text{ A}$)

V _{RWM}		Breakdown Voltage			V _C (Volts) (Note 7)				
Device	(Note 5)	I _R @ V _{RWM}	V_{BR}	(Note 6) (Volts)	@ I _T			
(Note 4)	(Volts)	(μΑ)	Min	Nom	Max	(mA)	@ I _{PP} = 120 A	@ I _{PP} = 60 A	@ I _{PP} = 30 A
1N5908	5.0	300	6.0	-	-	1.0	8.5	8.0	7.6

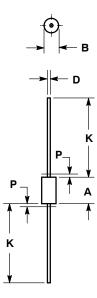
- 3. Square waveform, PW = 8.3 ms, Non-repetitive duty cycle.
- 4. 1N5908 is JEDEC registered as a unidirectional device only (no bidirectional option)
- 5. A transient suppressor is normally selected according to the maximum working peak reverse voltage (V_{RWM}), which should be equal to or greater than the dc or continuous peak operating voltage level.
- 6. VBR measured at pulse test current I_T at an ambient temperature of 25°C and minimum voltages in VBR are to be controlled.
- 7. Surge current waveform per Figure 4 and derate per Figure 2 of the General Data 1500 W at the beginning of this group

^{*}Bidirectional device will not be available in this device

1N5908

PACKAGE DIMENSIONS

MOSORB CASE 41A-04 ISSUE D



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. LEAD FINISH AND DIAMETER UNCONTROLLED IN DIMENSION P.
 4. 041A-01 THRU 041A-03 OBSOLETE, NEW STANDARD 041A-04.

	INC	HES	MILLIMETERS			
DIM	MIN	MAX	MIN	MAX		
Α	0.335	0.374	8.50	9.50		
В	0.189	0.209	4.80	5.30		
D	0.038	0.042	0.96	1.06		
K	1.000		25.40			
Р		0.050		1.27		